



(12) **Patent Application Publication**
MATSUI et al.

(43) **Pub. Date:** **Feb. 27, 2014**

USPC 349/42

(57) **ABSTRACT**

(30) **Foreign Application Priority Data**

Aug. 23, 2012 (JP) 2012-183705

Publication Classification

(51) **Int. Cl.**

G02F 1/1343

(2006.01)

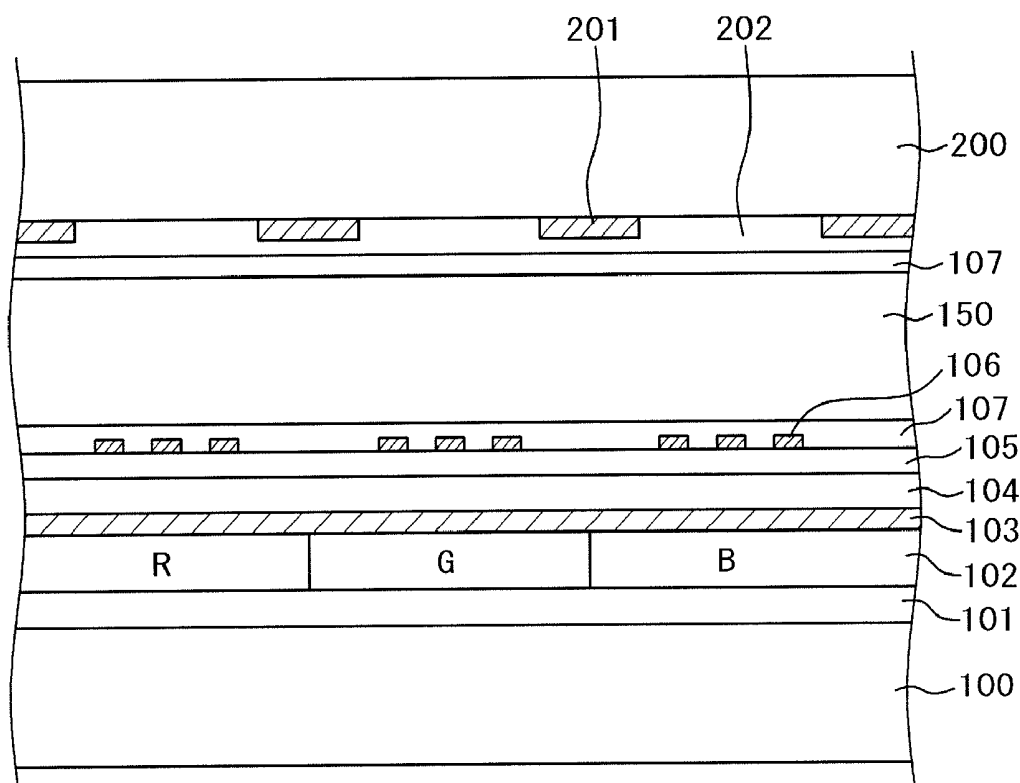


FIG. 1

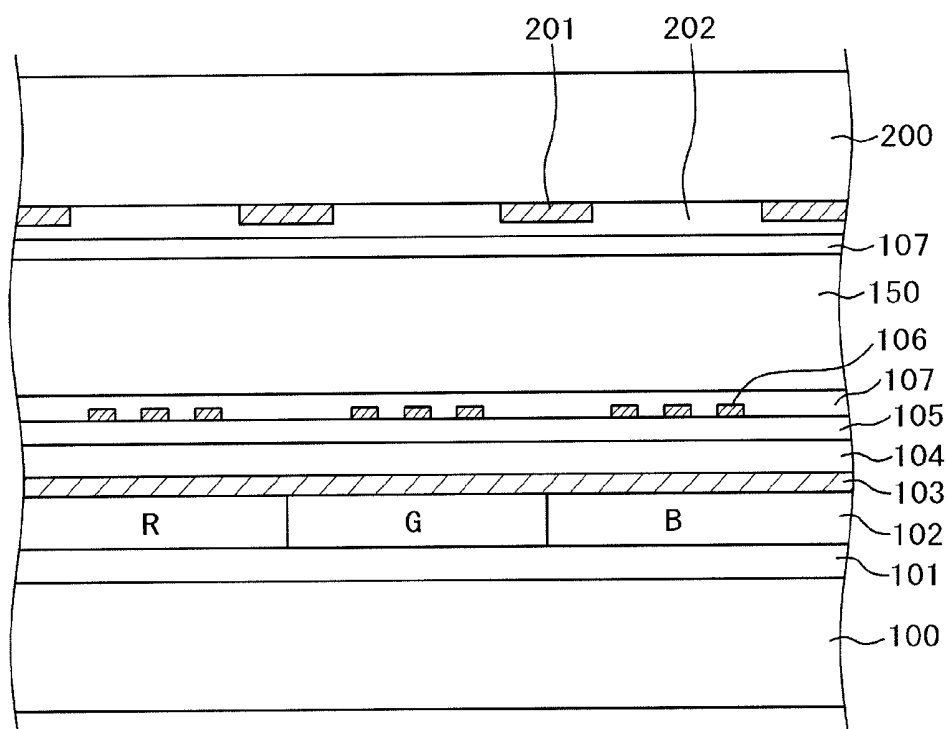


FIG. 2

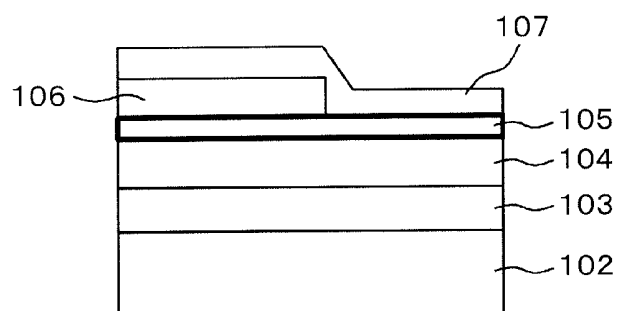


FIG. 3

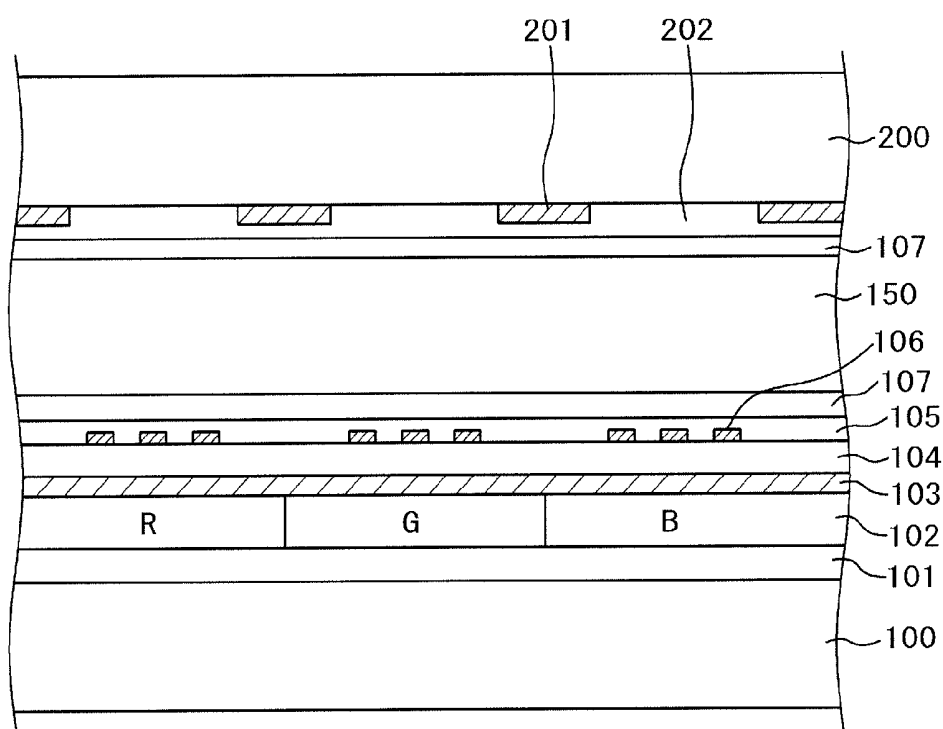


FIG. 4

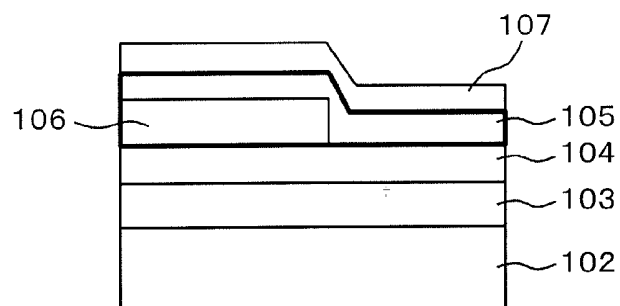


FIG. 5

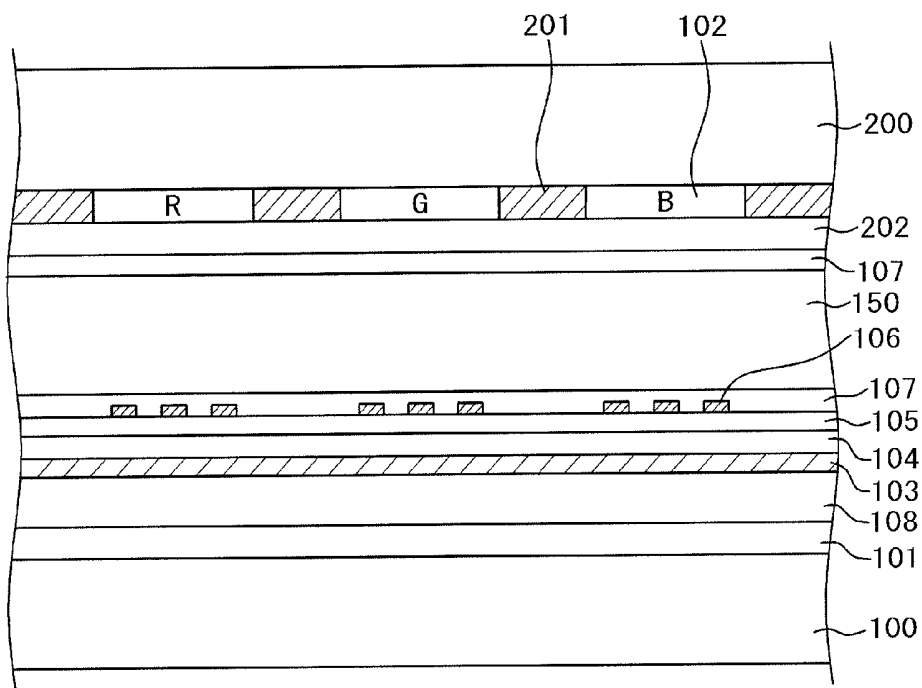


FIG. 6

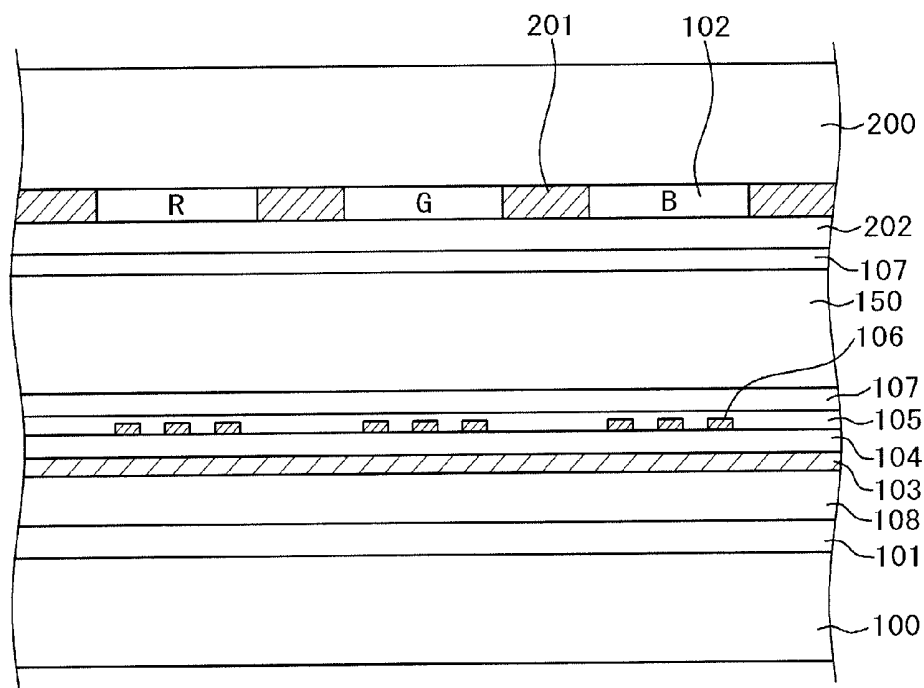


FIG. 7

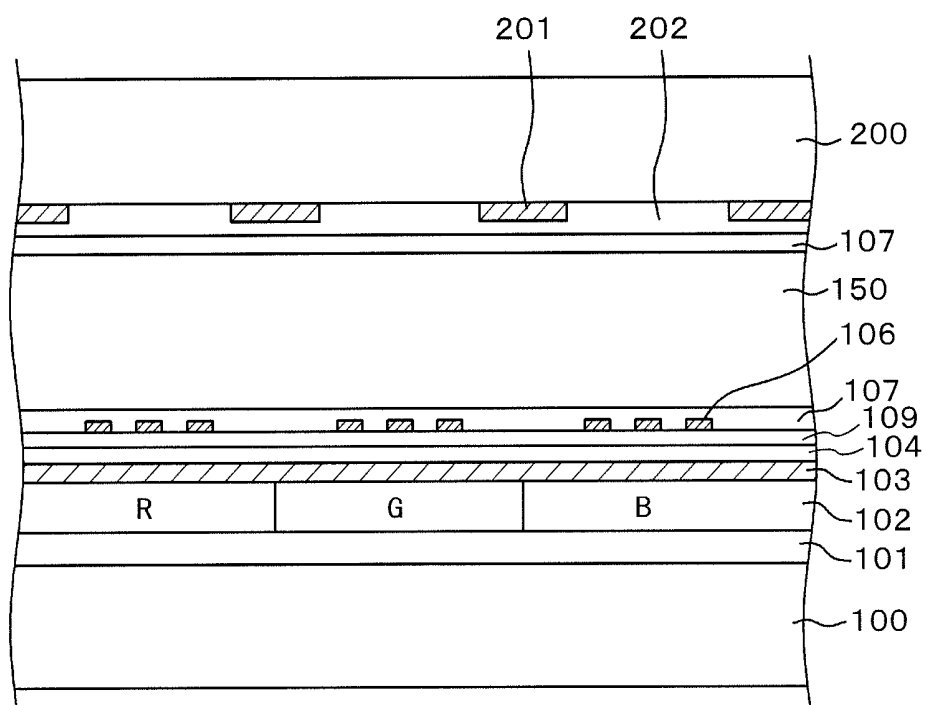


FIG. 8

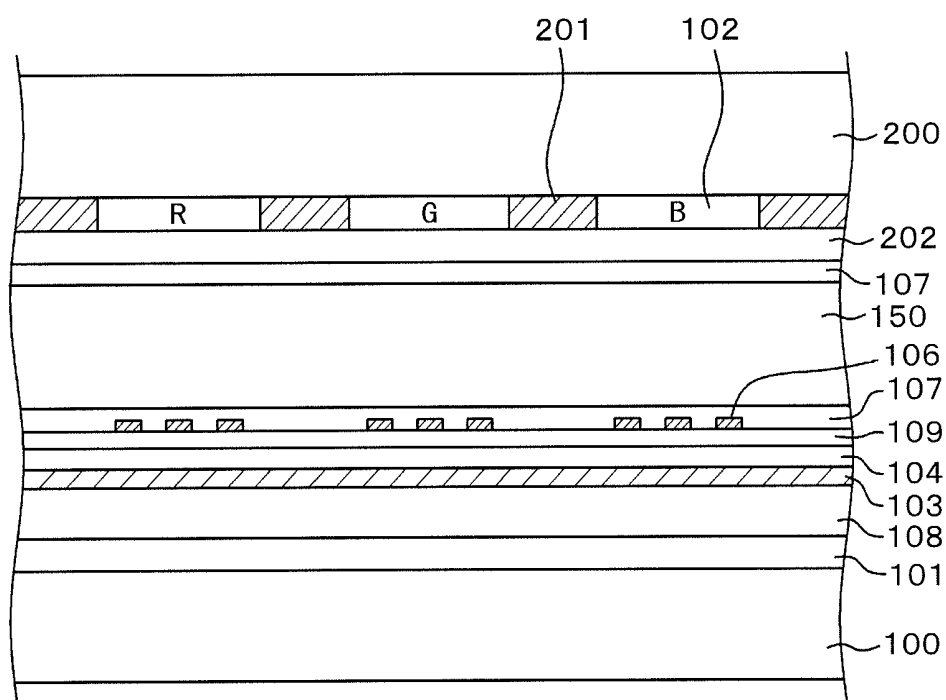


FIG. 9

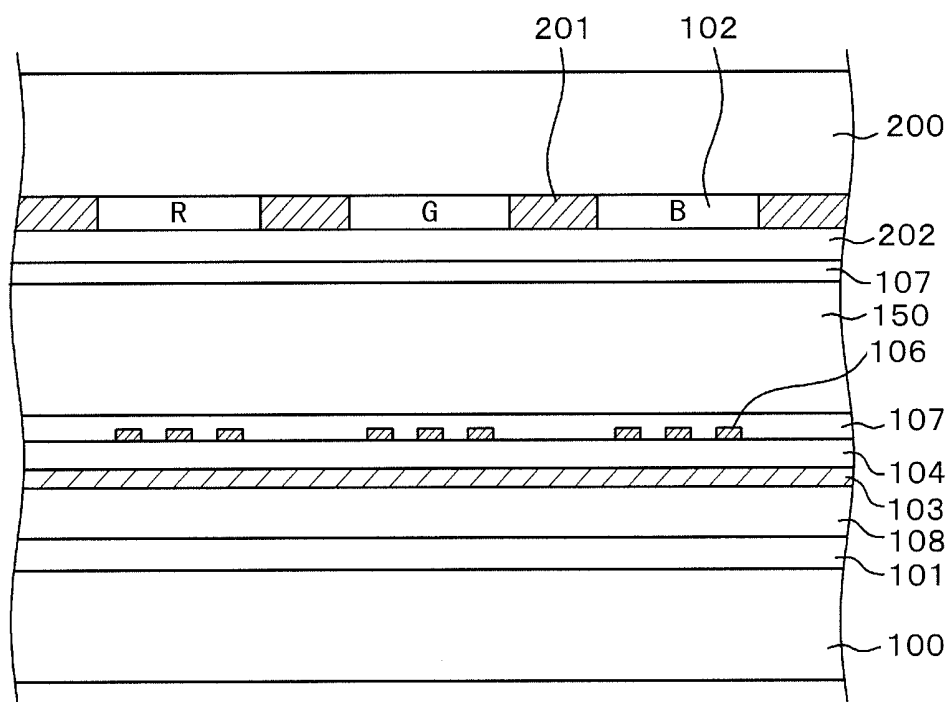


FIG. 10

BL-off	$\sim 10^{14} \Omega \cdot \text{cm}$
BL-on	$\sim 10^{12} \Omega \cdot \text{cm}$

FIG. 11

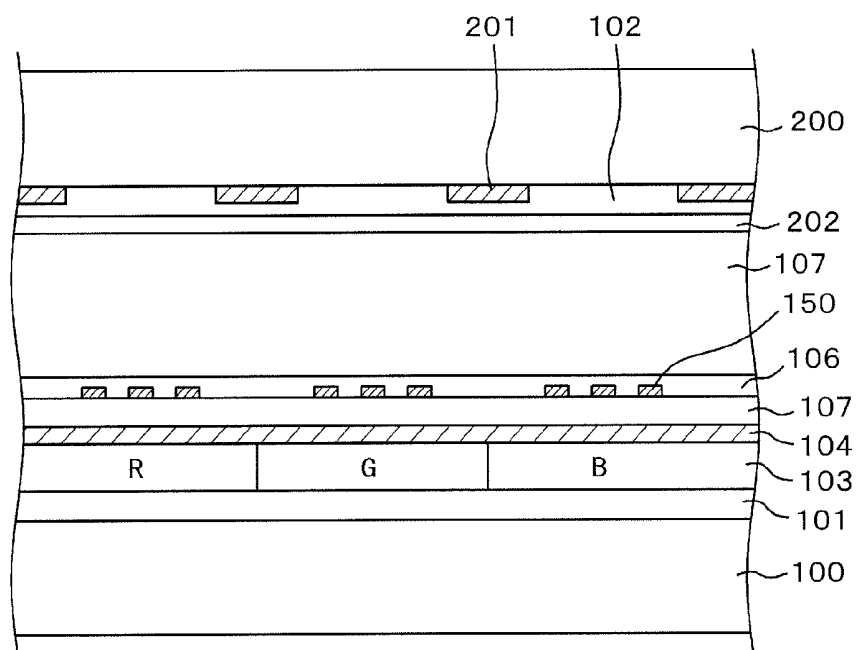


FIG. 12

R-PIXEL, G-PIXEL	$\sim 10^{14} \Omega \cdot \text{cm}$
B-PIXEL	$\sim 10^{12} \Omega \cdot \text{cm}$

LIQUID CRYSTAL DISPLAY DEVICE

CLAIM OF PRIORITY

[0001] The present application claims priority from Japanese Patent Application JP 2012-183705 filed on Aug. 23, 2012, the content of which is hereby incorporated by reference into this application.

BACKGROUND OF THE INVENTION

[0002] 1. Field of the Invention

[0003] The present invention relates to a display device. More particularly, the invention relates to a liquid crystal display device in which a countermeasure against afterimage phenomenon is taken, with the afterimage phenomenon occurring when a color filter is formed over a substrate where a pixel electrode is formed.

[0004] 2. Description of the Related Art

[0005] Since liquid crystal display devices can be reduced in thickness and weight, their application use has been extended to various fields including large-scaled devices such as television, and mobile phones and DSC (Digital Still Camera). On the other hand, the liquid crystal display devices have a problem of view angle characteristics. The view angle characteristic is a phenomenon in which brightness or chromaticity changes between a case in which a screen is observed from the front and a case in which the screen is observed in an oblique direction. For the view angle characteristics, an IPS (In Plane Switching) system for operating liquid crystal molecules by electric field in a horizontal direction has excellent characteristics.

[0006] A conventional liquid crystal display device includes a TFT substrate having a pixel electrode, thin film transistors (TFT), etc. formed in a matrix; a counter substrate disposed in facing relation to the TFT substrate and having a color filter, etc. formed at portions corresponding to the pixel electrodes of the TFT substrate; and liquid crystals put between the TFT substrate and the counter substrate. Images are formed by controlling the transmittance of light by liquid crystal molecules for every pixel.

[0007] However, in the conventional liquid crystal display devices described above, the TFT substrate and the counter substrate have to be positioned accurately. Therefore, the positioning step drives up the manufacturing cost of the liquid crystal display device. Further, since complete positioning is not possible between the TFT substrate and the counter substrate, a positioning margin is taken in view of design. To take the margin, since it is necessary to increase the area for a black matrix, this reduces the transmittance of a liquid crystal display panel to cause loss in the brightness of a screen. Further, formation of a screen having high fineness is also limited.

[0008] Then, a technique of forming a color filter on a TFT substrate has been developed. If the color filter is fabricated into the TFT substrate, the pixel electrode and the color filter can be positioned, for example, by a photolithographic step. Therefore, the accuracy is outstandingly higher compared with that in positioning between the TFT substrate and the counter substrate. Further, since the step of forming the color filter requires an identical step both in a case in which the color film is formed on the counter substrate and in a case in which the color film is formed on the TFT substrate, the number of step of forming the color filter is not increased.

[0009] Accordingly, by using a system for fabricating a color filter to a TFT substrate (color filter on array; hereinafter

referred to as COA), manufacturing cost can be reduced, and the screen brightness can be improved by improving the transmittance of the liquid crystal display device and a screen having high fineness can be achieved.

[0010] On the other hand, the liquid crystal display device involves a phenomenon of DC afterimage. This is a phenomenon that electric charges are accumulated on an alignment film when a certain image is displayed for a predetermined time and the image is observed as if it were burnt to the screen for a certain time. The lasting time of the DC afterimage can be shortened by reducing the electric resistance of the alignment film.

[0011] Since a backlight is used in the liquid crystal display device, the electric resistance of the alignment film during operation can be reduced by using a photoconductive material for the alignment film. Accordingly, a photoconductive alignment film is used in many recent liquid crystal display devices. Materials showing a photoconductive property as the alignment film include, for example, SE 6414 manufactured by Nissan Chemical Co.

[0012] However, in the COA, since the color filter is formed on the side of the backlight with respect to the alignment film, the intensity of a light from backlight reaching the alignment film is less than that in the conventional device. Accordingly, no sufficient photoconductivity can be provided to the alignment film and the resistance of the alignment film during operation cannot be reduced sufficiently. Accordingly, the DC afterimage causes a serious problem with the COA.

[0013] The alignment film absorbs more light at shorter wavelength because light at a short wavelength contributes to the photoconductivity. As the transmittance lowers at a short wavelength, there occurs a phenomenon that more light on the side of longer wavelength transmits through the alignment film or transmits through the liquid crystal display panel, and the image is shifted to the side of red color.

[0014] JP-A-2011-237571 describes a configuration for increasing the thickness of color filters in a COA in the order of a red filter, a green filter, and a blue filter, thereby preventing shifting of a screen image to the red color. Alternatively, it describes another configuration for increasing the size of pixels in the order of a red filter, a green filter, and a blue filter, thereby preventing the screen image from shifting to the red color.

SUMMARY OF THE INVENTION

[0015] In JP-A-2011-237571, it is necessary to change the size of pixels for every pixels of red, green, and blue, or change the thickness of the color filter. Then, when the absorption spectrum of the color filter changes for every kind or every material of the color filter, it is necessary to change the ratio of the thickness of each of color filters or the ratio of area of each of color filters for every kind or every material of color filter, which increases process load.

[0016] FIG. 9 is a cross sectional view of a conventional liquid crystal display panel in which a color filter 102 is formed on the side where a counter substrate 200 is provided. FIG. 10 is a table for comparing the specific resistivity of an alignment film 107 between a case where a backlight is turned off and a case where it is turned on in the liquid crystal display panel illustrated in FIG. 9. In FIG. 9, since the color filter 102 is formed on the side where the counter substrate 200 is provided, there is no difference in the photoconductive characteristic to the specific resistivity of the alignment film 107 due to the color filter 102.

[0017] In FIG. 10, the specific resistivity of the alignment film SE6414 is 10^{14} Ωcm when the backlight is turned off and the specific resistivity thereof is 10^{12} Ωcm when the backlight is turned on.

[0018] FIG. 11 is a cross sectional view of a conventional liquid crystal display panel in which a color filter 102 is formed on the side where a TFT substrate 100 is provided. In FIG. 11, the color filter 102 is formed on an interconnect layer 101 of the TFT substrate 100, and a counter electrode 103, a pixel electrode 106, alignment film 107, etc. are formed thereon. In FIG. 11, a black matrix 201, an overcoat film 202, and an alignment film 107 are formed on a counter substrate 200 but the color filter 102 is not formed.

[0019] In FIG. 11, a backlight is applied to the back of the TFT substrate 100. In this configuration, since the light from the backlight is absorbed by the color filter 102, no sufficient photoconductivity can be provided to the alignment film 107. Further, since the photoconductivity of the alignment film 107 has the wavelength dependence, the photoconductive property of the alignment film 107 is different for every pixel to cause color shift in the screen.

[0020] FIG. 12 is a table for evaluating the photoconductive effect for every color when the backlight is applied. In the alignment film of FIG. 12, the specific resistivity scarcely changes even when the film is irradiated with the backlight in a case of a red pixel and a green pixel, whereas the specific resistivity is decreased by two digits for the blue pixel. This shows that the color shift occurs when the afterimage is caused.

[0021] The present invention intends to prevent occurrence of afterimage caused by accumulation of electric charges on the alignment film in a COA where a color filter is disposed on the side where a TFT substrate 100 is provided. The present invention further intends to achieve a configuration for preventing color shift of an afterimage in the COA without changing the thickness of the color filter 102 or changing the size of the pixel for every color.

[0022] To overcome the problems described above, the present invention provides the following specific configurations.

[0023] (1) A liquid crystal display device includes: a TFT substrate; a color filter; a counter electrode; an interlayer insulation film; a pixel electrode; an alignment film; a liquid crystal layer; a counter substrate; and a Si semiconductor layer, the color filter, the counter electrode, the interlayer insulation film, the pixel electrode, and the alignment film being formed on the side where the TFT substrate is provided, the counter substrate being disposed in facing relation to the TFT substrate with the liquid crystal layer put between the counter substrate and the TFT substrate. The Si semiconductor layer is formed between the pixel electrode and the interlayer insulation layer.

[0024] (2) A liquid crystal display device includes: a TFT substrate; a color filter; a counter electrode; an interlayer insulation film; a pixel electrode; an alignment film; a liquid crystal layer; a counter substrate; and a Si semiconductor layer, the color filter, the counter electrode, the interlayer insulation film, the pixel electrode, and the alignment film being formed on the side where the TFT substrate is provided, the counter substrate being disposed in facing relation to the TFT substrate with the liquid crystal layer put between the counter substrate and the TFT substrate. The Si semiconductor layer is formed between the pixel electrode and the alignment film.

[0025] (3) A liquid crystal display device includes: a TFT substrate; a counter electrode; an interlayer insulation film; a pixel electrode; an alignment film; a liquid crystal layer; a counter substrate having a color filter formed therein; and a Si semiconductor layer, the counter electrode, the interlayer insulation film, the pixel electrode, and the alignment film being formed on the side where the TFT substrate is provided, the counter substrate being disposed in facing relation to the TFT substrate with the liquid crystal layer put between the counter substrate and the TFT substrate. The Si semiconductor layer is formed between the pixel electrode and the interlayer insulation film.

[0026] (4) A liquid crystal display device includes: a TFT substrate; a counter electrode; an interlayer insulation film; a pixel electrode; an alignment film; a liquid crystal layer; a counter substrate having a color filter formed therein; and a Si semiconductor layer, the counter electrode, the interlayer insulation film, the pixel electrode, and the alignment film being formed on the side where the TFT substrate is provided, the counter substrate being disposed in facing relation to the TFT substrate with the liquid crystal layer put between the counter substrate and the TFT substrate. The Si semiconductor layer is formed between the pixel electrode and the alignment film.

[0027] (5) In a liquid crystal display device, an oxide semiconductor having a resistance equal to that of the Si semiconductor layer is formed instead of the Si semiconductor layer.

[0028] According to the invention, DC afterimage can be suppressed in an IPS liquid crystal display device using a COA system having a color filter formed on the side where a TFT substrate is provided. Further, in the liquid crystal display device as in the usual device having the color filter formed on the side where the counter electrode is provided, since electric charges accumulated on the alignment film can escape not relying on the photoconductive effect, color shift of the DC afterimage can be suppressed. The alignment film to be used may be either a rubbing alignment film or an optical alignment film, and the invention is not restricted in view of the material and the alignment process.

BRIEF DESCRIPTION OF THE DRAWINGS

[0029] FIG. 1 is a cross sectional view of a liquid crystal display panel of a first embodiment;

[0030] FIG. 2 is a cross sectional view illustrating the operation of the first embodiment;

[0031] FIG. 3 is a cross sectional view of a liquid crystal display panel of a second embodiment;

[0032] FIG. 4 is a cross sectional view illustrating the operation of the second embodiment;

[0033] FIG. 5 is a cross sectional view of a liquid crystal display panel of a third embodiment;

[0034] FIG. 6 is a cross sectional view of a liquid crystal display panel of a fourth embodiment;

[0035] FIG. 7 is a cross sectional view of a liquid crystal display panel of a fifth embodiment,-

[0036] FIG. 8 is a cross sectional view of a liquid crystal display panel of a sixth embodiment;

[0037] FIG. 9 is a cross sectional view of a liquid crystal display panel in a first conventional embodiment;

[0038] FIG. 10 is a table illustrating a photoelectric effect of an alignment film in the first conventional embodiment;

[0039] FIG. 11 is a cross sectional view of a liquid crystal display panel of a second conventional embodiment; and

[0040] FIG. 12 is a table illustrating a photoelectric effect of an alignment film in the second conventional embodiment.

DESCRIPTION OF THE PREFERRED EMBODIMENTS

[0041] The present invention is to be described specifically by way of the following preferred embodiments.

First Embodiment

[0042] FIG. 1 is a cross sectional view of a liquid crystal display panel according to a first embodiment of the invention. FIG. 1 illustrates an IPS liquid crystal display panel which is a COA type liquid crystal display panel having a color filter 102 formed on the side where a TFT substrate 100 is provided. In FIG. 1, an interconnect layer 101 is formed on a TFT substrate 100 formed of glass. The interconnect layer 101 includes TFTs, video signal lines, scanning lines, etc.

[0043] In FIG. 1, a red color filter 102, a green color filter 102, and a blue color filter 102 are formed for every pixel on the interconnect layer 101. A counter electrode 103 comprising ITO (Indium Tin Oxide) formed as a flat solid electrode is formed on the color filter 102. An interlayer insulation film 104 comprising SiN is formed on the counter electrode 103. The SiN film is formed by a low temperature CVD at about 200° C.

[0044] A Si semiconductor layer 105 is formed on the interlayer insulation film 104, and this is a feature of the invention. The Si semiconductor layer 105 may be an intrinsic semiconductor or a semiconductor doped with P or the like. The Si semiconductor layer 105 has a thickness of 5 nm to 100 nm.

[0045] A comb-shaped pixel electrode 106 comprising ITO is formed on the Si semiconductor 105, and an alignment film 107 is formed thereover. If the resistance of the alignment film 107 is high, electric charges remain for a long time on the alignment film 107, which causes an afterimage. For erasing the afterimage in an early stage, the electric charges can escape in an early stage by reducing the resistance of the Si semiconductor layer 105 formed under the alignment film 107 in addition to reduction in the resistance of the alignment film 107.

[0046] In FIG. 1, a counter substrate 200 is disposed in facing relation to the TFT substrate 100 with a liquid crystal layer 150 put between them. A black matrix 201 is formed on the counter substrate 200 formed of glass, and an overcoat film 202 is formed so as to cover the black matrix 201. The color filter 102 is not formed between a black matrix 201 and another black matrix 201. An alignment film 107 is formed on the overcoat film 202.

[0047] FIG. 2 is an enlarged cross sectional view for explaining the operation of the configuration illustrated in FIG. 1. In FIG. 2, a counter electrode 103 comprising ITO is formed as a flat solid electrode on a color filter 102, an interlayer insulation film 104 comprising SiN is formed thereon, a semiconductor layer 105 is formed thereon, a comb-shaped pixel electrode 106 comprising ITO is further formed thereon, and an alignment film 107 is formed so as to cover the pixel electrode 106.

[0048] Since the interlayer insulation film 104 comprising SiN is formed by CVD after formation of the color filter 102 comprising an organic material, it is formed by a low temperature CVD at about 200° C. for preventing denaturation of the color filter 102. The semiconductor layer 105 formed over the interlayer insulation film 104 comprises a-Si. Since the

interlayer insulation film 104 comprising SiN and the Si semiconductor layer 105 are formed continuously by CVD, this decreases burden on the process even when the present invention is applied.

[0049] Since the resistance of the alignment film 107 is as high as about $10^{14} \Omega \text{cm}$, it takes a long time for electric charge accumulated on the alignment film 107 to escape to the pixel electrode 106, etc. In FIG. 2, the Si semiconductor layer 105 is formed under the alignment film 107 and even if the Si semiconductor layer 105 is an intrinsic semiconductor, the specific resistivity thereof is lower by one digit or more than that of the material for the alignment film. Accordingly, even when no sufficient light from a back light is applied to the alignment film 107 and the photoelectric effect cannot be provided sufficiently, the electric charges accumulated on the alignment film 107 can escape by way of the underlying Si semiconductor layer 105 to the pixel electrode 106 and the afterimage can be erased in an early stage.

[0050] Since the thickness of the alignment film 107 is about 50 to 70 nm, the resistance of the alignment film 107 in the direction of the thickness is not high. Accordingly, electric charges moving from the surface of the alignment film 107 can move through the underlying Si semiconductor layer 105 to the pixel electrode 106, resulting in early erasure of the afterimage. The erasure time of the afterimage can be controlled by the extent of the resistance of the Si semiconductor layer 105 and this can be controlled by the thickness of the Si semiconductor layer 105 and whether P or the like is doped or not to the Si semiconductor layer 105.

[0051] In the invention, since the resistance value of the alignment film per se is not reduced by the photoelectric effect, it is not necessary that the photoelectric effect of the alignment film is large. When the resistance value is reduced relying on the photoelectric effect, since the color filter has spectral characteristics, wavelength dependence occurs in the resistance of the alignment film to cause color shift in the afterimage. Since the invention does not rely on the photoelectric effect of the alignment film, color shift is not caused in the afterimage. Further, the material for the alignment film can be selected optimally in accordance with the purpose of the alignment film with no consideration for on photoelectric effect.

[0052] The configuration of this embodiment is different from the conventional configuration in that the Si semiconductor layer 105 is formed after formation of the interlayer insulation film 104 comprising SiN and then the pixel electrode 106 is formed. Since SiN is formed by so-called low temperature CVD and the Si semiconductor layer 105 is also formed by CVD, the Si semiconductor layer 105 can be formed continuously after deposition of the interlayer insulation film 104 comprising SiN by CVD. Accordingly, this decreases burden on the process.

Second Embodiment

[0053] FIG. 3 is a cross sectional view of a liquid crystal display panel according to a second embodiment of the invention. A color filter 102 is formed on the side where a TFT substrate 100 provided and not formed on the side where a counter substrate 200 is provided. A configuration of FIG. 3 is different from the configuration of FIG. 1 in that an interlayer insulation film 104 comprising SiN is formed on a counter electrode 103 formed as a flat solid electrode, and a comb-shaped pixel electrode 106 is formed thereon and a Si semi-

conductor layer **105** is formed over a pixel electrode **106**. Then, an alignment film **107** is formed on the Si semiconductor layer **105**.

[0054] In FIG. 3, electric charges accumulated on the alignment film **107** which cause the afterimage escape to the side where the pixel electrode **106** is provided by way of a Si semiconductor layer **105** formed under the alignment film **107**. Since the specific resistivity of the Si semiconductor layer **105** is lower by one digit or more than that of the alignment film **107**, electric charges accumulated on the alignment film **107** are erased in an early stage through the Si semiconductor layer **105** and also the afterimage is erased in an early stage.

[0055] FIG. 4 is an enlarged schematic cross sectional view for explaining the operation of the constitution of FIG. 3. In FIG. 4, a counter electrode **103** comprising ITO is formed as a flat solid electrode on a color filter **102**, an interlayer insulation film **104** comprising SiN is formed thereon, and a pixel electrode **106** is formed further thereon. After patterning of the pixel electrode **106** into a comb-shaped electrode by photolithography, a Si semiconductor layer **105** is formed.

[0056] The Si semiconductor layer **105** has a thickness of about 5 to 100 nm. Such a thickness that causes entire step disconnection by the pixel electrode **106** comprising ITO may cause a problem in terms of operation. However, partial step disconnection may be allowed. It may suffice that the pixel electrode **106** and the Si semiconductor **105** are in electric conduction.

[0057] Since the resistance of the alignment film **107** is as high as about 10^{14} Ωcm , it takes a long time for electric charges formed on the alignment film **107** to escape to the pixel electrode **106**, etc. In FIG. 4, a Si semiconductor layer **105** is formed under the alignment film **107** and even if the Si semiconductor layer **105** is an intrinsic semiconductor, the specific resistivity of the Si semiconductor layer **105** is lower by one digit or more than that of the material for the alignment film. Accordingly, even when no sufficient light from a backlight is applied to the alignment film **107** and the photoelectric effect cannot be provided sufficiently, electric charges accumulated on the alignment film **107** can escape by way of the underlying Si semiconductor layer **105** to the pixel electrode **106** and the afterimage can be erased in an early stage. The erasure time of the afterimage can be controlled by controlling the extent of the resistance of the Si semiconductor layer **105** and this can be controlled by the thickness of the Si semiconductor layer **105** and whether P or the like is doped to the Si semiconductor layer **105**.

[0058] Also in this embodiment, since escape of the electric charges accumulated on the alignment film does not rely on the reduction of the resistance by the photoelectric effect of the alignment film per se but relies on the Si semiconductor layer formed to the underlying layer, color shift of the afterimage under the effect of the spectral characteristic of the color filter can be suppressed.

[0059] In this embodiment, after the interlayer insulation film **104** is formed, the pixel electrode **106** is formed by depositing ITO and patterning the same by using a photolithography. Subsequently, the Si semiconductor layer **105** is deposited by CVD. That is, after the interlayer insulation film **104** is deposited by CVD and an ITO film is formed as the pixel electrode **106**, the TFT substrate **100** is taken out from a vacuum atmosphere into atmospheric air and ITO is patterned. Then, the Si semiconductor layer **105** is deposited again by CVD.

[0060] As described above, the burden on the process is larger in the second embodiment compared with that in the first embodiment. However, the advantageous effect is identical.

Third Embodiment

[0061] FIG. 5 is a cross sectional view illustrating a third embodiment according to the invention. In FIG. 5, an interconnect layer **101** is formed on a TFT substrate **100** formed of glass. The interconnect layer **101** includes TFTs, video signal lines, scanning lines, etc. An organic passivation film **108** is formed on the interconnect layer **101**, and a counter electrode **103** comprising ITO is formed as a flat solid electrode thereon. An interlayer insulation film **104** comprising SiN is formed on the counter electrode **103** and a Si semiconductor layer **105** is formed thereon. A comb-shaped pixel electrode **106** is formed on the Si semiconductor layer **105**, and an alignment film **107** is formed so as to cover the pixel electrode. While SiN that forms the interlayer insulation film **104** is formed by CVD, since the insulation film is formed after the organic passivation film **108** is formed, this is formed by a so-called low temperature CVD at about 200° C.

[0062] In FIG. 5, a black matrix **201** and a color filter **102** are formed on a counter substrate **200** formed of glass, and an overcoat film **202** is formed so as to cover the black matrix **201** and the color filter **102**. An alignment film **107** is formed so as to cover the overcoat film **202**.

[0063] In the configuration of FIG. 5, the color filter **102** is formed to the counter substrate **200** as in the conventional device. That is, light from a backlight is not shielded by the color filter **102**. However, also in the conventional embodiment illustrated in FIG. 5, electric charges are accumulated on the alignment film **107** to cause an afterimage. In the conventional device, the resistance of the alignment film **107** is decreased by using a material having a photoelectric effect for the alignment film **107**.

[0064] However, also in the conventional device, there is a limit to the reduction of the resistance of the alignment film **107** by the photoelectric effect. Then, a two-layered structure was adopted for the alignment film **107** by using a layer of an alignment film having high alignment property but having a high resistivity as an upper layer and using an alignment material having a resistivity lower than that of the upper layer as a lower layer. However, it is necessary in this method to synthesize a material suitable to a process of forming two-layered alignment film by coating the material for the alignment film for once, and there was a problem of impairing the degree of freedom in the selection of the material for the alignment film.

[0065] In the invention illustrated in FIG. 5, a Si semiconductor layer **105** is formed under a comb-shaped pixel electrode **106** and an alignment film **107** is formed above the pixel electrode. Even when the Si semiconductor layer **105** is an intrinsic semiconductor, the specific resistivity of the semiconductor layer is lower by one digit or more than the specific resistivity of the alignment film.

[0066] Accordingly, electric charges accumulated on the alignment film **107** can escape in an early stage to the pixel electrode **106** without the production of the photoelectric effect in the alignment film **107**. That is, the electric charges accumulated on the alignment film **107** can stably escape in an early stage to the pixel electrode, etc. irrespective of the intensity of light from the backlight.

[0067] How the electric charges accumulated on the alignment film **107** can escape to the pixel electrode **106** in an early stage is the same as described with reference to the schematic cross sectional view of FIG. **2**. Further, also the thickness, the specific resistivity, and whether doping is necessary or not to the Si semiconductor layer **105** are as has been described with reference to FIG. **2** for the first embodiment. Therefore, according to this embodiment, the afterimage can be erased stably in an early stage even in a liquid crystal display panel having the color filter **102** formed on the side where the counter substrate **200** is provided.

[0068] Also in this embodiment, since SiN that forms the interlayer insulation film **104** is formed by CVD and the Si semiconductor layer **105** is also formed by CVD, the Si semiconductor layer **105** can be formed continuously after deposition of SiN by CVD. Accordingly, this decreases burden on the process.

Fourth Embodiment

[0069] FIG. **6** is a cross sectional view of a liquid crystal display panel according to a fourth embodiment of the invention. In FIG. **6**, a color filter **102** is formed on the side where a counter substrate **200** is provided as in the conventional case in the same manner as in FIG. **5**. The configuration illustrated in FIG. **6** is different from the configuration illustrated in FIG. **5** in view of the cross sectional view showing the vicinity of a pixel electrode **106**. In FIG. **6**, a comb-shaped pixel electrode **106** is formed on an interlayer insulation film **104**. A Si semiconductor layer **105** is formed over the pixel electrode **106**, and an alignment film **107** is formed on the Si semiconductor layer **105**.

[0070] Also in this configuration, since the specific resistivity of the Si semiconductor layer **105** is lower by one digit or more than the specific resistivity of the alignment film **107**, electric charges accumulated on the alignment film **107** can escape through the Si semiconductor layer **105** to the pixel electrode **106**, etc. Accordingly, the afterimage can be erased in an early stage.

[0071] How the electric charges accumulated on the alignment film **107** escape to the pixel electrode **106** in the configuration of FIG. **6** is the same as described in the second embodiment with reference to FIG. **4**. Further, also the forming process in the vicinity of the pixel electrode **106** is as has been described above with reference to FIG. **4**. Since this embodiment has no configuration of using the two-layered structure for the alignment film **107** and utilizing the photoelectric effect, the electric charges accumulated on the alignment film **107** can escape in an early stage to the pixel electrode **106** irrespective of the intensity of light from a backlight and the effect of the afterimage can be erased in an early stage.

[0072] In the embodiments described above, the counter electrode **103** is formed as a flat solid electrode in the underlying layer, the interlayer insulation film **104** is formed thereon, and the comb-shaped pixel electrode **106** is formed thereon. However, the invention is not restricted only to such embodiments but is applicable also to a configuration in which the pixel electrode **106** is formed as a flat solid electrode in the underlying layer, the interlayer insulation film **104** is formed thereon, and the comb-shaped counter electrode **103** is formed thereon.

Fifth Embodiment

[0073] FIG. **7** is a cross sectional view of a liquid crystal display panel according to a fifth embodiment of the inven-

tion. A color filter **102** is formed on the side where a TFT substrate **100** is provided but not formed on the side where a counter substrate **200** is provided. FIG. **7** is different from FIG. **1** in that an oxide semiconductor layer **109** showing a resistance equal to that of the Si semiconductor layer is formed instead of the Si semiconductor layer formed under an alignment film **107**. Examples of the oxide semiconductor include ITO and the like. Erasure time of the afterimage can be controlled by the extent of the resistance of the oxide semiconductor layer **109** and this can be controlled by the thickness of the oxide semiconductor layer **109** and an oxygen concentration during film formation.

[0074] In the embodiment illustrated in FIG. **7**, the oxide semiconductor layer **109** formed on the interlayer insulation film **104** comprises ITO. Since the oxide semiconductor layer **109** and the pixel electrode **106** are formed continuously by sputtering, this decreases burden on the process even when the invention is applied.

Sixth Embodiment

[0075] FIG. **8** is a cross sectional view of a liquid crystal display panel according to a sixth embodiment of the invention. In FIG. **8**, a color filter **102** is formed on the side where a counter substrate **200** is provided as in FIG. **5**. The embodiment illustrated in FIG. **8** is different from the embodiment illustrated in FIG. **5** in that an oxide semiconductor layer **109** showing a resistance equal to that of the Si semiconductor layer is formed instead of the Si semiconductor layer formed under an alignment film **107**. Examples of the oxide semiconductor include ITO and the like in the same manner as in FIG. **7**. How the electric charges accumulated in the alignment film **107** can escape to the pixel electrode **106** in an early stage is the same as described with reference to the schematic cross sectional view shown in FIG. **2**. The film thickness, the specific resistivity, the film forming conditions etc. for the oxide semiconductor layer **109** are identical with those explained with reference to FIG. **7** for the fifth embodiment. Therefore, according to this embodiment, the afterimage can be erased stably in an early stage also in a liquid crystal panel having the color filter **102** formed on the side where the counter substrate **200** is provided as in the usual device.

[0076] In the embodiments described above, the material for the alignment film may be either a rubbing alignment film or an optical alignment film, and the invention is applicable with no restriction to material and alignment process.

What is claimed is:

1. A liquid crystal display device comprising: a TFT substrate; a color filter; a counter electrode; an interlayer insulation film; a pixel electrode; an alignment film; a liquid crystal layer; a counter substrate; and a Si semiconductor layer,

the color filter, the counter electrode, the interlayer insulation film, the pixel electrode, and the alignment film being formed on the side where the TFT substrate is provided,

the counter substrate being disposed in facing relation to the TFT substrate with the liquid crystal layer put between the counter substrate and the TFT substrate, wherein the Si semiconductor layer is formed between the pixel electrode and the interlayer insulation layer.

2. A liquid crystal display device comprising: a TFT substrate; a color filter, a counter electrode; an interlayer insulation film; a pixel electrode; an alignment film; a liquid crystal layer; a counter substrate; and a Si semiconductor layer,

the color filter, the counter electrode, the interlayer insulation film, the pixel electrode, and the alignment film being formed on the side where the TFT substrate is provided,

the counter substrate being disposed in facing relation to the TFT substrate with the liquid crystal layer put between the counter substrate and the TFT substrate, wherein the Si semiconductor layer is formed between the pixel electrode and the alignment film.

3. A liquid crystal display device comprising: a TFT substrate; a counter electrode; an interlayer insulation film; a pixel electrode; an alignment film; a liquid crystal layer; a counter substrate having a color filter formed therein; and a Si semiconductor layer,

the counter electrode, the interlayer insulation film, the pixel electrode, and the alignment film being formed on the side where the TFT substrate is provided,

the counter substrate being disposed in facing relation to the TFT substrate with the liquid crystal layer put between the counter substrate and the TFT substrate, wherein the Si semiconductor layer is formed between the pixel electrode and the interlayer insulation film.

4. A liquid crystal display device comprising: a TFT substrate; a counter electrode; an interlayer insulation film; a pixel electrode; an alignment film; a liquid crystal layer; a counter substrate having a color filter formed therein; and a Si semiconductor layer,

the counter electrode, the interlayer insulation film, the pixel electrode, and the alignment film being formed on the side where the TFT substrate is provided,

the counter substrate being disposed in facing relation to the TFT substrate with the liquid crystal layer put between the counter substrate and the TFT substrate,

wherein the Si semiconductor layer is formed between the pixel electrode and the alignment film.

5. The liquid crystal display device according to claim 1, wherein

the Si semiconductor layer comprises a-Si.

6. The liquid crystal display device according to claim 2, wherein

the Si semiconductor layer comprises a-Si.

7. The liquid crystal display device according to claim 3, wherein

the Si semiconductor layer comprises a-Si.

8. The liquid crystal display device according to claim 4, wherein

the Si semiconductor layer comprises a-Si.

9. The liquid crystal display device according to claim 1, wherein

the Si semiconductor layer has a thickness of 5 nm to 100 nm.

10. The liquid crystal display device according to claim 2, wherein

the Si semiconductor layer has a thickness of 5 nm to 100 nm.

11. The liquid crystal display device according to claim 3, wherein

the Si semiconductor layer has a thickness of 5 nm to 100 nm.

12. The liquid crystal display device according to claim 4, wherein

the Si semiconductor layer has a thickness of 5 nm to 100 nm.

* * * * *

专利名称(译)	液晶显示装置		
公开(公告)号	US20140055701A1	公开(公告)日	2014-02-27
申请号	US13/964133	申请日	2013-08-12
[标]申请(专利权)人(译)	株式会社日本显示器		
申请(专利权)人(译)	日本展示INC.		
当前申请(专利权)人(译)	日本展示INC.		
[标]发明人	MATSUI CHIKAE YAMAMOTO MASANAO KUNIMATSU NOBORU SONODA HIDEHIRO		
发明人	MATSUI, CHIKAE YAMAMOTO, MASANAO KUNIMATSU, NOBORU SONODA, HIDEHIRO		
IPC分类号	G02F1/1343		
CPC分类号	G02F1/134309 G02F1/1333 G02F1/136 G02F2001/133397 G02F2001/136222 G02F2001/134372		
优先权	2012183705 2012-08-23 JP		
其他公开文献	US9304362		
外部链接	Espacenet USPTO		

摘要(译)

在液晶显示装置中，包括：TFT基板;滤色镜;反电极;层间绝缘膜;像素电极;配向膜;液晶层;对衬底;和Si半导体层。滤色器，对电极，层间绝缘膜，像素电极和取向膜形成在设置TFT基板的一侧，对置基板与TFT基板面对，液晶层置于计数器之间在基板和TFT基板上，在像素电极和层间绝缘膜之间形成Si半导体层。即使来自背光的光被滤色器吸收并且足够的光不能到达取向膜，累积在取向膜上的电荷也可以通过形成在取向膜下面的Si半导体层在早期逃逸到像素电极，从而能够在早期阶段消除残像。

